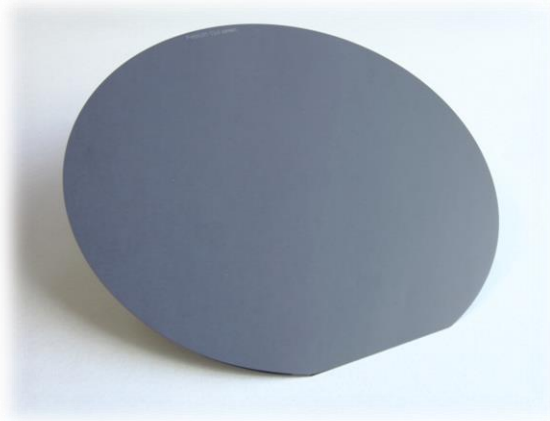
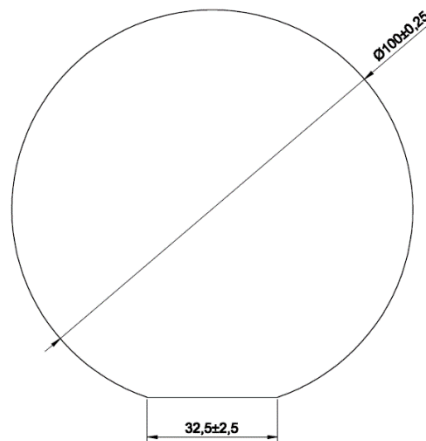




30% Triple Junction GaAs Epitaxial Wafer Type: TJ GaAs Epitaxial Wafer 3G30W-Advanced



The AZUR SPACE unprocessed Epitaxial Wafers of class 30% contain our high-efficiency GaInP/GaAs/Ge based epitaxial layers on a Ge substrate. These epitaxial wafers can be used for any further processing and customized cell designs.



30% Triple Junction GaAs Epitaxial Wafer-Advanced

Type: TJ GaAs Epitaxial Wafer 3G30W-Advanced



Design and Mechanical Data

Base Material	GalnP/GaAs/Ge on Ge substrate
Dimensions	100 mm ± 0.25 mm
Thickness	150 μm ± 20 μm or 175 μm ± 20 μm
Major Flat length	32.5 mm ± 2.5 mm
Major Flat orientation	<100> ± 2°
Average Weight	≤ 80 mg/cm ²
Excluded area	2 mm rim from the outer wafer edge
Laser mark label	Alpha-numeric



Electrical Data*

		BOL	2.5E14	5E14	1E15
Average Open Circuit V_{oc}	[mV]	2700	2616	2564	2522
Average Short Circuit I_{sc}	[mA/cm ²]	17.2	17.2	17.0	16.6
Voltage at max. Power V_{mp}	[mV]	2411	2345	2290	2246
Current at max. Power I_{mp}	[mA/cm ²]	16.7	16.7	16.6	16.1
Average Efficiency η_{bare} (1367 W/m ²)	[%]	29.5	28.6	27.8	26.5
Average Efficiency η_{bare} (1353 W/m ²)	[%]	29.8	28.9	28.1	26.8

Acceptance Values

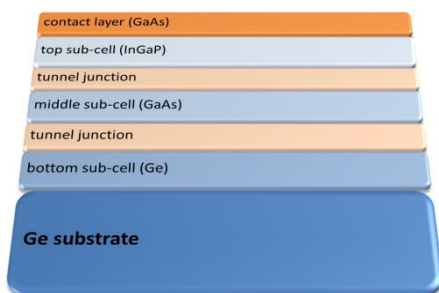
Averaged Efficiency per lot	29.5 %
Min. average Efficiency per wafer	27.5 %



Temperature Gradients

		BOL	2.5E14	5E14	1E15
Open Circuit Voltage	$\Delta V_{oc}/\Delta T \uparrow$ [mV/°C]	- 6.2	- 6.5	- 6.6	- 6.7
Short Circuit Current	$\Delta I_{sc}/\Delta T \uparrow$ [mA/°C]	0.36	0.33	0.35	0.38
Voltage at max. Power	$\Delta V_{mp}/\Delta T \uparrow$ [mV/°C]	- 6.7	- 6.8	- 7.1	- 7.2
Current at max. Power	$\Delta I_{mp}/\Delta T \uparrow$ [mA/°C]	0.24	0.20	0.24	0.28

Layer Structure



Typical IV-Curve

